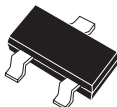




CMPTA29

**HIGH VOLTAGE
NPN SILICON
DARLINGTON TRANSISTOR**



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPTA29 is a Silicon NPN Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high voltage and high gain.

Marking Code is C29.

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

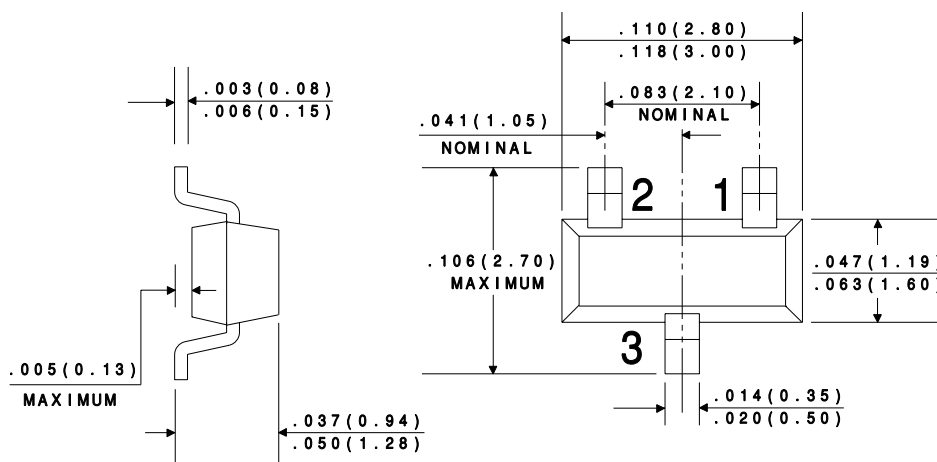
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CES}	100	V
Emitter-Base Voltage	V_{EBO}	12	V
Collector Current	I_C	500	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CES}	$V_{CE}=80\text{V}$		500	nA
I_{CBO}	$V_{CB}=80\text{V}$		100	nA
I_{EBO}	$V_{BE}=10\text{V}$		100	nA
BV_{CES}	$I_C=100\mu\text{A}$	100		V
BV_{CBO}	$I_C=100\mu\text{A}$	100		V
BV_{EBO}	$I_E=10\mu\text{A}$	12		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=10\mu\text{A}$		1.2	V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=100\text{mA}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$		2.0	V

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=5.0V$, $I_C=10mA$	10,000		
h_{FE}	$V_{CE}=5.0V$, $I_C=100mA$	10,000		
f_T	$V_{CE}=5.0V$, $I_C=10mA$, $f=100MHz$	125		MHz
C_{ob}	$V_{CB}=10V$, $I_E=0$, $f=1.0MHz$		8.0	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR